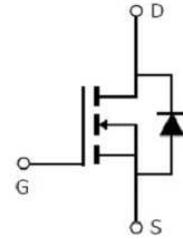


**Main Product Characteristics:**

$V_{DSS}$	75V
$R_{DS(on)}$	6.5mohm(typ.)
$I_D$	80A


**TO220**

**Marking and pin Assignment**

**Schematic diagram**
**Features and Benefits:**

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 175°C operating temperature


**Description:**

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

**Absolute max Rating:**

Symbol	Parameter	Max.	Units
$I_D @ TC = 25\text{ }^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$ ①	80	A
$I_D @ TC = 100\text{ }^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$ ①	70	
$I_{DM}$	Pulsed Drain Current②	320	
$P_D @ TC = 25\text{ }^\circ\text{C}$	Power Dissipation③	200	W
	Linear Derating Factor	2.0	W/°C
$V_{DS}$	Drain-Source Voltage	75	V
$V_{GS}$	Gate-to-Source Voltage	± 20	V
$E_{AS}$	Single Pulse Avalanche Energy @ L=0.3mH	375	mJ
$I_{AS}$	Avalanche Current @ L=0.3mH	50	A
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 175	°C